TECHNICAL DATA DATA SHEET 1177, REV. B

## THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: A 50/100/150 VOLT, 15 AMP, 40 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at  $T_A = 25^{\circ}$ C unless otherwise specified.

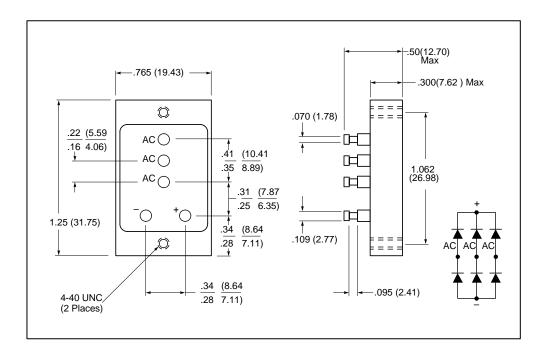
RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-		Vdc
S10A305HE S10A310HE S10A315HE				50 100 150	
Average DC Output Current (T <sub>C</sub> = Case Temp) (I <sub>o</sub> )	$T_{C} = 55 ^{\circ}\text{C}$ $T_{C} = 100 ^{\circ}\text{C}$ $T_{C} = 125 ^{\circ}\text{C}$	-	-	15 9.0 5.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I <sub>o</sub> )	$T_A = 25$ °C $T_A = 55$ °C $T_A = 100$ °C	-	-	4.75 3.75 2.25	Amps
Peak Single Cycle Surge Current (I <sub>FSM</sub> )	t <sub>p</sub> = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current (I <sub>FRM</sub> )	$T_A = 25$ °C	-	-	35	Amps
Operating and Storage Temp. ( $T_{op}$ & $T_{stq}$ )	-	-55	-	+150	°C
Maximum Forward Voltage (V <sub>f</sub> )	I <sub>f</sub> = 6.0A (300 μsec pulse, duty cycle < 2%)	-	-	1.0	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	T <sub>A</sub> = 25° C T <sub>A</sub> = 100° C	-	-	10 100	μAmps
Reverse Recovery Time (t <sub>rr</sub> )	$I_f = 0.5A, I_r = 1.0A, I_{rr}$ = 0.25A	-	-	40	nsec
Thermal Resistance (θ <sub>JL</sub> )	-	-	-	3.0	°C/W

<sup>•</sup> World Wide Web - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •

## SENSITRON

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## **MECHANICAL DIMENSIONS: In Inches / mm**



Notes: Case finish - Black Anodized Potted dimension - uncontrolled

FIG. 410

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